

Reverse Costing analysis



Epson Toyocom X3500W 1-Axis QMEMS Gyroscope

February 2010 - Version 1

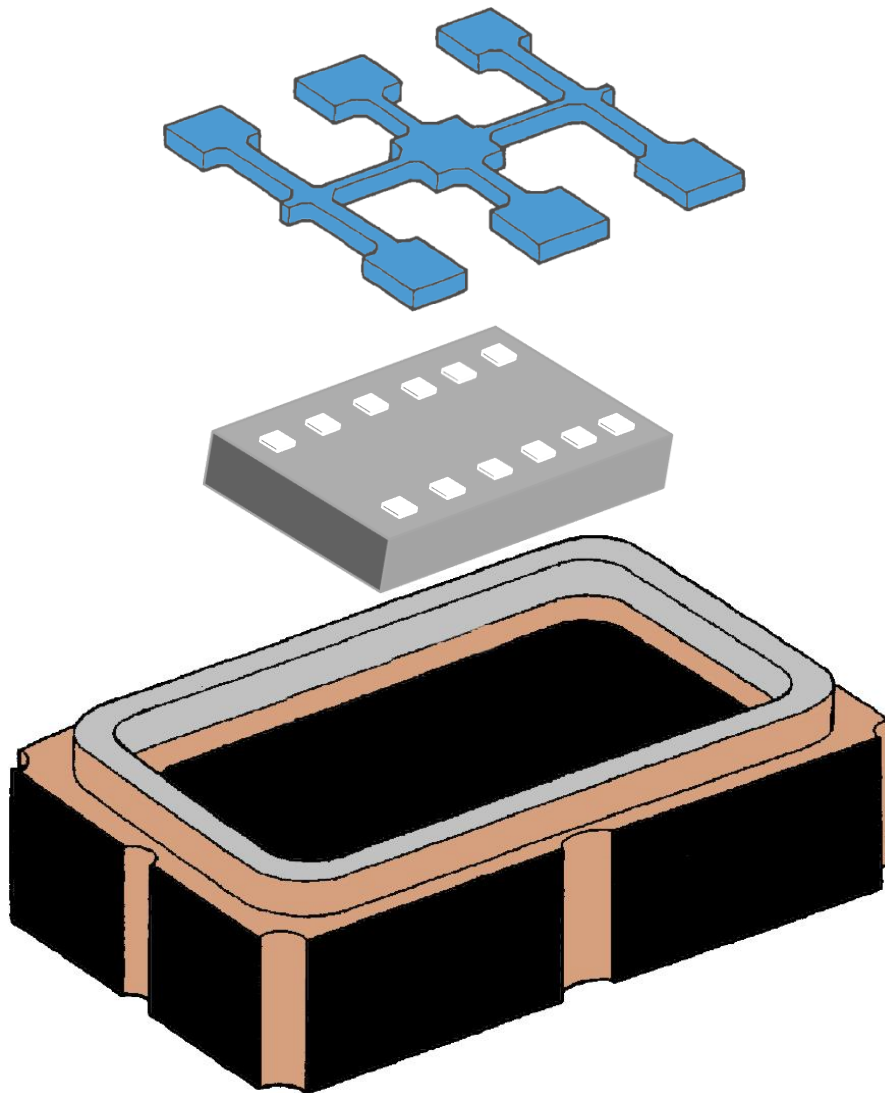
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- 2 dies assembled in a CLCC package are used to build the X3500W component



QMEMS

- ✓ Quartz Substrate
- ✓ Bulk Micro-Machining
- ✓ Lithography steps

ASIC

- ✓ Silicon Substrate
- ✓ CMOS 0.18µm process
- ✓ 1.5µm CMOS 1.8V
- ✓ Lithography steps

Package

- ✓ CLCC-8
- ✓ Multi-Chip
- ✓ Hermetic Encapsulation

The reverse costing analysis is conducted in 3 phases:

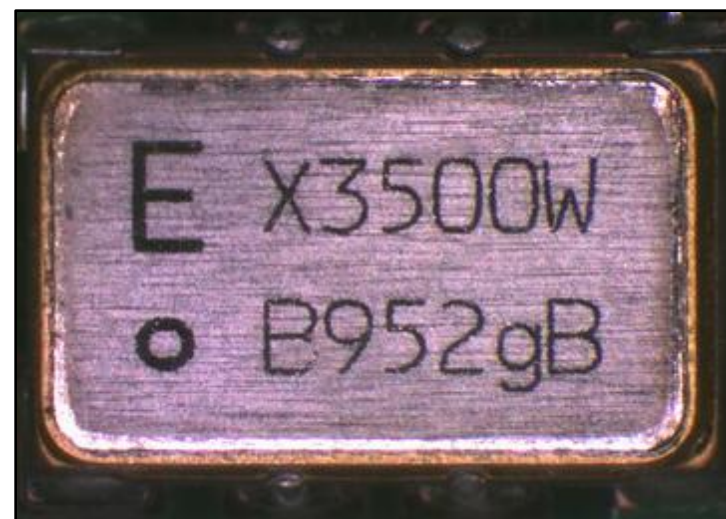
<ul style="list-style-type: none"> • Package is analyzed and measured. • The dies are extracted in order to get overall data: dimensions, main blocks, pad number and pin out, die marking • Set up of the manufacturing process. 	Teardown analysis
<ul style="list-style-type: none"> • Setup of the manufacturing environment • Cost simulation of the process steps with different year scenarios 	Costing analysis
<ul style="list-style-type: none"> • Supply Chain Analysis • Analysis of the selling price 	Selling price analysis

- Epson Toyocom Gyro Sensor product line :

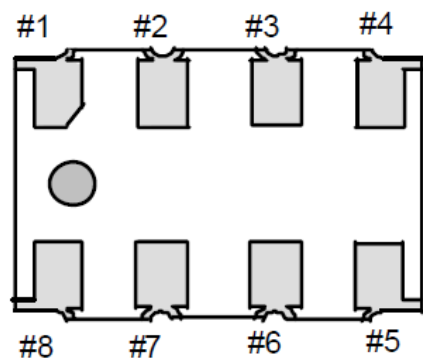


Model	Package	Dimensions	Operating voltage	Bias	Rate Range	Scale Factor
XV-8100CB	Ceramic LCC-8	5.0mm x 3.2mm x 1.3mm	3.0V	1350mV	+/- 100 deg/s	2.5 mV/(°·s ⁻¹)
XV-8000LK	Plastic LCC-8	6.0mm x 4.8mm x 3.3mm	5.0V	50% Vdd	+/- 60 deg/s	25 mV/(°·s ⁻¹)
XV-8000CB	Ceramic LCC-8	5.0mm x 3.2mm x 1.3mm	5.0V	50% Vdd	+/- 60 deg/s	25 mV/(°·s ⁻¹)
XV-3500CB	Ceramic LCC-8	5.0mm x 3.2mm x 1.3mm	3.0V	1350mV	+/- 100 deg/s	0.67 mV/(°·s⁻¹)

- **Package type:** Ceramic LCC 8-pin SMD hermetically sealed
- **Dimensions:** 5.00mm x 3.20mm x 1.3mm
- **Pin pitch:** 1.27mm
- **Marking :**
 - E** X3500W
 - o** B952gB

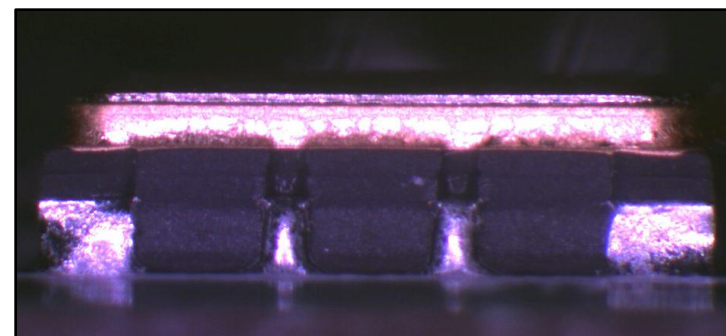


Package Top view

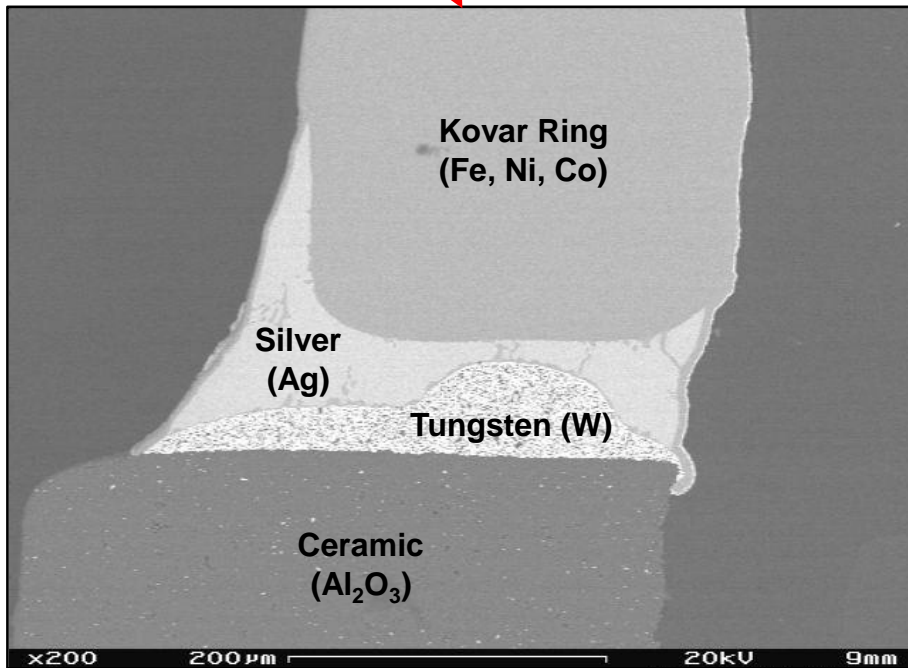
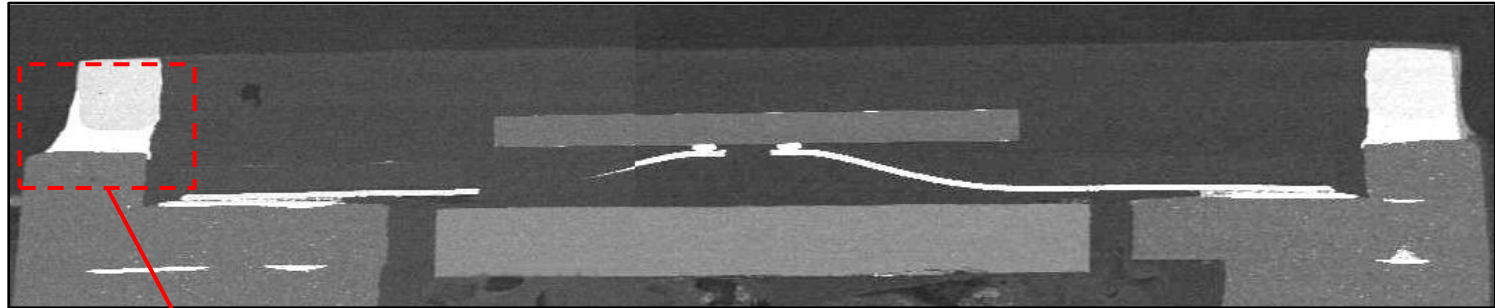


Pin	Connection
1	N.C.
2	N.C.
3	N.C.
4	GND
5	V _{OUT}
6	V _{REF}
7	Sleep
8	V _{DD}

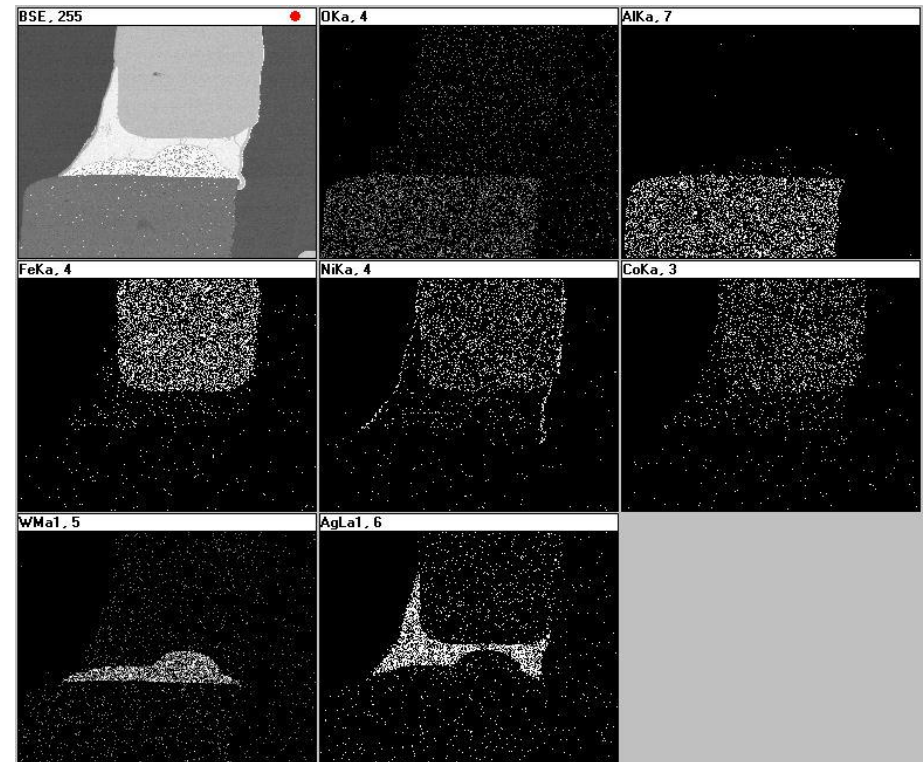
Supposed Pin Map (according to XV-3500CB Datasheet)



Package Side view



Component Cross-Section



SEM-EDX

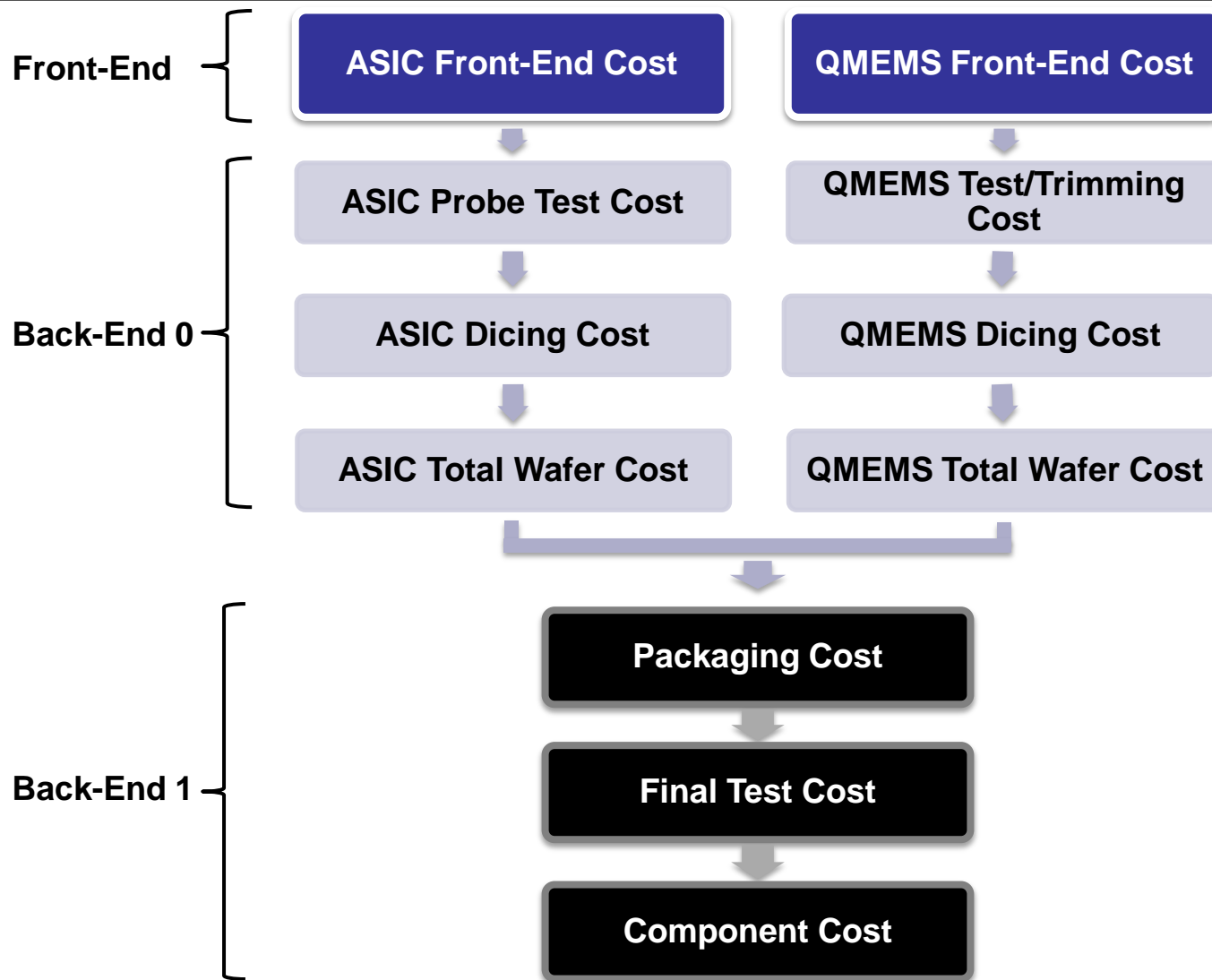
• Double-T Structure Formation:

- ✓ **Substrate:** Quartz wafer
- ✓ **Process type:** Bulk micromachining
- ✓ **Metal layers:** 100nm Chromium/Gold
- ✓ **Lithography steps:** 2

The manufacturing of the Cap begins with the etching of the wafer to define the cavity. Then the wafer is patterned and etched to create the cavity. An aluminum layer (100nm) is then deposited on the top of wafer. A hard mask (SiO₂) is then deposited, patterned and etched. The cavity of the cap is then etched by a RIE etching process. An oxide layer is finally deposited on the back of wafer for the front bonding with the sensor wafer.

• Double-T Structure Formation

- ✓ [Step 1]
- ✓ [Step 2]
- ✓ [Step 3]
- ✓ [Step 4]
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- ✓ [Step 100]



- We perform the economic analysis of the ASIC with the [IC Purchaser](#) software.
- We perform the economic analysis of the MEMS and the packaging with the [MEMS CoSim+](#) software.

QMEMS Manufacturing	Low Yield		Medium Yield		High Yield	
	Cost	Breakdown	Cost	Breakdown	Cost	Breakdown
Raw wafer (Quartz)						
Clean Room						
Equipment						
Consumable						
Salary						
Yield losses						
QMEMS Manufacturing Cost						

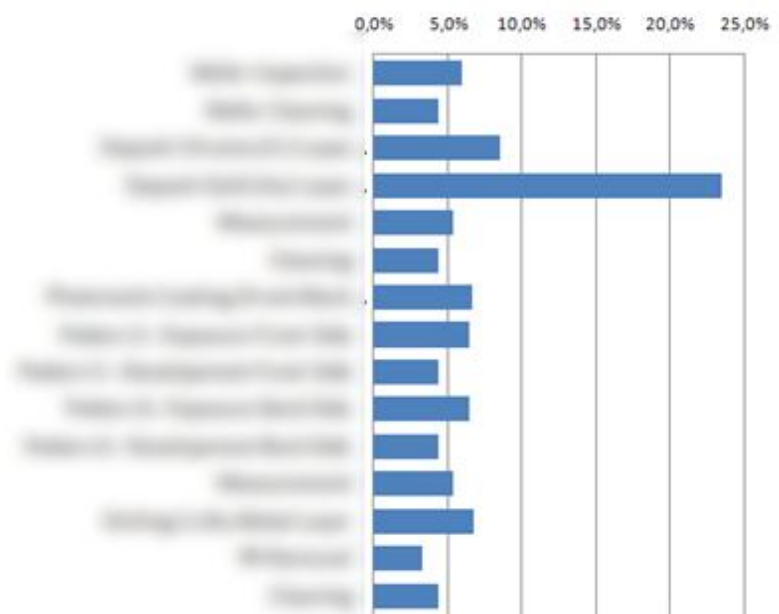
QMEMS Manufacturing Cost Breakdown (Middle Yield)



- The QMEMS Front-End manufacturing cost range from \$xx to \$xx according to yield variations.
- The main part of the manufacturing cost is due to the xxx with xx%.
- The manufacturing yield ranges from xx% to xx%.

Electrodes Formation	Cost	Breakdown
Electrode 1	0,20	6,0%
Electrode 2	0,18	4,4%
Electrode 3	0,27	8,5%
Electrode 4	0,95	23,5%
Electrode 5	0,28	5,3%
Electrode 6	0,18	4,4%
Electrode 7	0,27	6,7%
Electrode 8	0,42	6,5%
Electrode 9	0,18	4,4%
Electrode 10	0,28	6,5%
Electrode 11	0,18	4,4%
Electrode 12	0,28	5,3%
Electrode 13	0,27	6,7%
Electrode 14	0,10	3,2%
Electrode 15	0,18	4,4%
Total	3,33	

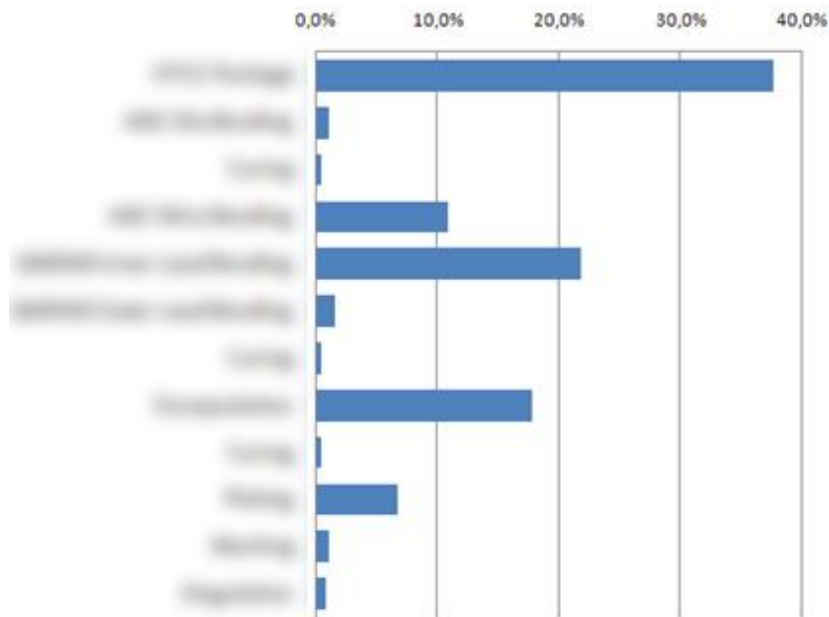
Electrodes Formation Step Cost Breakdown



Electrodes Formation Steps Cost
(Simulated with MEMS CoSim+ Cost Simulation Tool)

Packaging Step	Cost	Breakdown
...	...	37,7%
...	...	1,0%
...	...	0,4%
...	...	10,8%
...	...	21,8%
...	...	1,5%
...	...	0,4%
...	...	17,7%
...	...	0,4%
...	...	6,7%
...	...	0,9%
...	...	0,7%
Packaging Cost	...	100%

Packaging Step Cost Breakdown



Packaging Steps Cost

(Simulated with MEMS CoSim+ Cost Simulation Tool)

-The consumables cost represent 40% of the packaging cost (materials, gold bondings, epoxy, etc...)

-The equipment depreciation and maintenance cost represent 30% of the packaging cost.

-The clean room depreciation cost represents 7% of the packaging cost.

-The salary part is 15%.